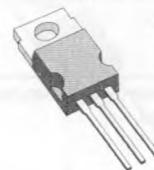


SWITCHING APPLICATIONS GENERAL PURPOSE

DESCRIPTION

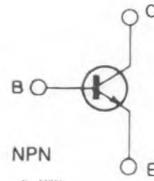
The D44H series are silicon multiepitaxial planar transistors and are mounted in Jedec TO-220 plastic package.

They are intended for various switching and general purpose applications.



TO-220

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		D44H 1/2	D44H 4/5	D44H 7/8	D44H 10/11	
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	30	45	60	80	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)			5		V
I_C	Collector Current			10		A
I_{CM}	Collector Peak Current			20		A
P_{tot}	Total Power Dissipation $T_{case} \leq 25^\circ\text{C}$			50		W
T_{stg}	Storage Temperature			-55 to 150		°C
T_j	Junction Temperature			150		°C

THERMAL DATA

$R_{th(j-case)}$	Thermal Resistance Junction-case	Max	2.5	C/W
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ELECTRICAL CHARACTERISTICS($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = \text{Rated } V_{CEO}$			10	μA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = \text{Rated } V_{EBO}$			100	μA
$V_{CEO(sus)}^*$	Collector-emitter Sustaining Voltage	$I_C = 100 \text{ mA}$ for D44H1/2 for D44H4/5 for D44H7/8 for D44H10/11	30 45 60 80			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 8 \text{ A}$ for D44H2/5/8/11 $I_C = 8 \text{ A}$ for D44H1/4/7/10	$I_B = 0.4 \text{ A}$ $I_B = 0.8 \text{ A}$		1 1	V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 8 \text{ A}$	$I_B = 0.8 \text{ A}$		1.5	V
h_{FE}^*	DC Current Gain	$V_{CE} = 1 \text{ V}$ for D44H1/4/7/10 for D44H2/5/8/11 $V_{CE} = 1 \text{ V}$ for D44H1/4/7/10 for D44H2/5/8/11	$I_C = 2 \text{ A}$ 35 60 $I_C = 4 \text{ A}$ 20 40			

* Pulsed pulse duration = 300 μs . duty cycle = 1.5%.